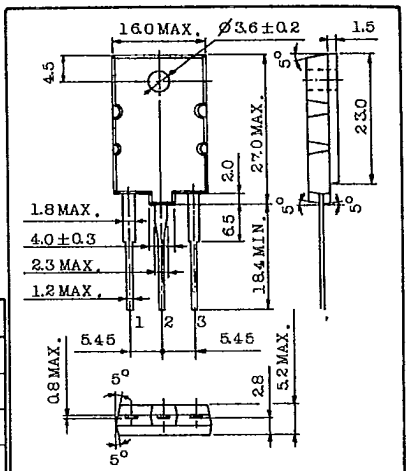
SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SD1430

COLOR TV HORIZONTAL OUTPUT APPLICATIONS.

FEATURES:
- High Voltage : V_{CBO}=1500V
- Low Saturation Voltage : $V_{CE(sat)}$=4V (Typ.) (I_C=3A, I_B=0.8A)
- High Speed : t_f=1.0μs (Max.) (I_{CP}=3A, $I_{B1(end)}$=0.8A)
- Glass Passivated Collector-Base Junction

Unit in mm



JEDEC	–
EIAJ	–
TOSHIBA	2-16D1A

Weight : 5.2g

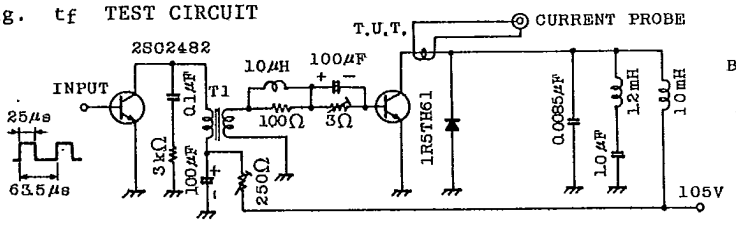
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	1500	V
Collector-Emitter Voltage	V_{CEO}	600	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	3.5	A
Emitter Current	I_E	-3.5	A
Collector Power Dissipation (Tc=25°C)	P_C	80	W
Junction Temperature	T_j	150	°C
Storage Temeprature Range	T_{stg}	-55~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=500V, I_E=0	–	–	10	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	–	–	1	mA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=0.5A	8	20	–	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=3A, I_B=0.8A	–	4	8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=3A, I_B=0.8A	–	–	1.5	V
Transition Frequency	f_T	V_{CE}=10V, I_C=0.1A	–	3	–	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	–	95	–	pF
Fall Time (Fig.)	t_f	I_{CP}=3A, $I_{B1(end)}$=0.8A	–	0.5	1.0	μs

Fig. t_f TEST CIRCUIT



TOSHIBA CORPORATION

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